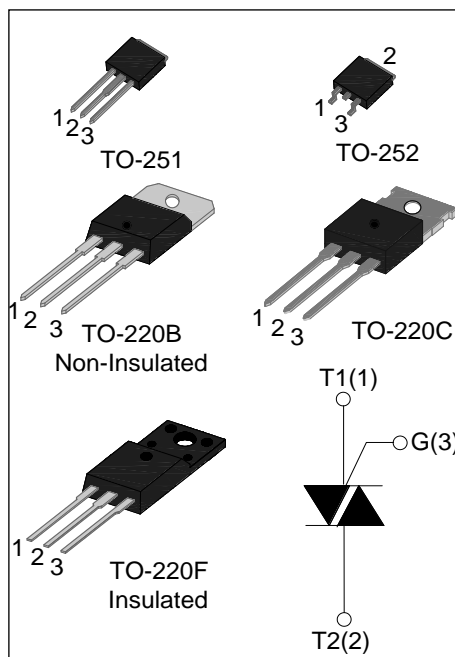




### DESCRIPTION:

JST136 series triacs with low holding and latching current are especially recommended for use on middle and small resistance type power load. JST136F provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).



### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
$V_{DRM}/V_{RRM}$	600 and 800	V

### ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40-150	°C
Operating junction temperature range		$T_j$	-40-125	°C
Repetitive peak off-state voltage( $T_j=25^\circ\text{C}$ )		$V_{DRM}$	600/800	V
Repetitive peak reverse voltage( $T_j=25^\circ\text{C}$ )		$V_{RRM}$	600/800	V
Non repetitive surge peak Off-state voltage		$V_{DSM}$	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		$V_{RSM}$	$V_{RRM} + 100$	V
RMS on-state current	TO-251/ TO-252 ( $T_C=110^\circ\text{C}$ )	$I_{T(RMS)}$	4	A
	TO-220B(Non-Ins)/ TO-220C( $T_C=107^\circ\text{C}$ )			
	TO-220F(Ins) ( $T_C=90^\circ\text{C}$ )			
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$ )		$I_{TSM}$	25	A
$I^2t$ value for fusing ( $t_p=10\text{ms}$ )		$I^2t$	3.1	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )	I - II -III	di/dt	50	A/ $\mu\text{s}$
	IV		10	

Peak gate current	$I_{GM}$	2	A
Average gate power dissipation	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	5	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^{\circ}C$  unless otherwise specified)

Symbol	Test Condition	Quadrant		Value			Unit
				D	E	F	
$I_{GT}$	$V_D=12V$	I - II - III	MAX	5	10	25	mA
		IV		10	25	70	
$V_{GT}$		ALL	MAX	1.5			V
$V_{GD}$	$V_D=V_{DRM} T_j=125^{\circ}C$ $R_L=3.3K\Omega$	ALL	MIN	0.2			V
$I_L$	$I_G=1.2I_{GT}$	I - III - IV	MAX	20	30	40	mA
		II		35	45	60	
$I_H$	$I_T=100mA$		MAX	15	25	30	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}C$		MIN	5	50	50	V/ $\mu s$
(dV/dt)c	(dI/dt)c=1.7A/ms $T_j=125^{\circ}C$		MIN	0.1	0.5	5	V/ $\mu s$

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=5.5A$ tp=380 $\mu s$	$T_j=25^{\circ}C$	1.7	V
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}C$	10	$\mu A$
$I_{RRM}$		$T_j=125^{\circ}C$	1	mA

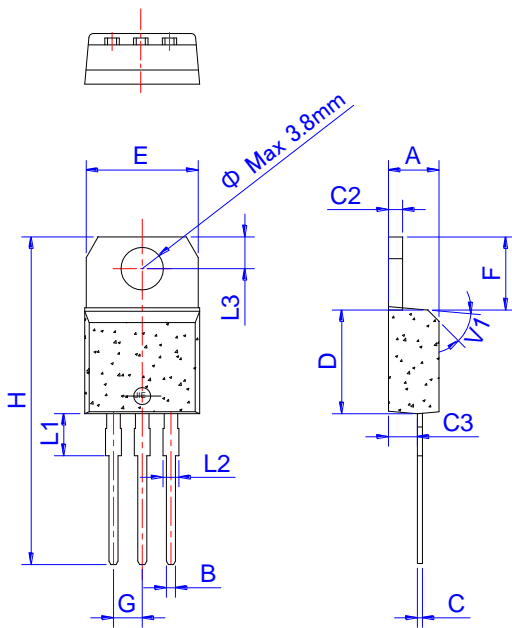
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251/ TO-252	4.0	$^{\circ}C/W$
		TO-220B(Non-Ins)/ TO-220C	3.0	
		TO-220F(Ins)	3.3	

ORDERING INFORMATION

J	ST	136	B	-600	E
JieJie Microelectronics Co.,Ltd	TRIACs	$I_{T(RMS)}:4A$ C:TO-220C F:TO-220F(Ins) B:TO-220B(Non-Ins) H:TO-251 K:TO-252		600: $V_{DRM}/V_{RRM} \geq 600V$ 800: $V_{DRM}/V_{RRM} \geq 800V$	T: $I_{GT1-4} \leq 5mA$ D: $I_{GT1-3} \leq 5mA$ $I_{GT4} \leq 10mA$ E: $I_{GT1-3} \leq 10mA$ $I_{GT4} \leq 25mA$ C: $I_{GT1-3} \leq 25mA$ $I_{GT4} \leq 50mA$

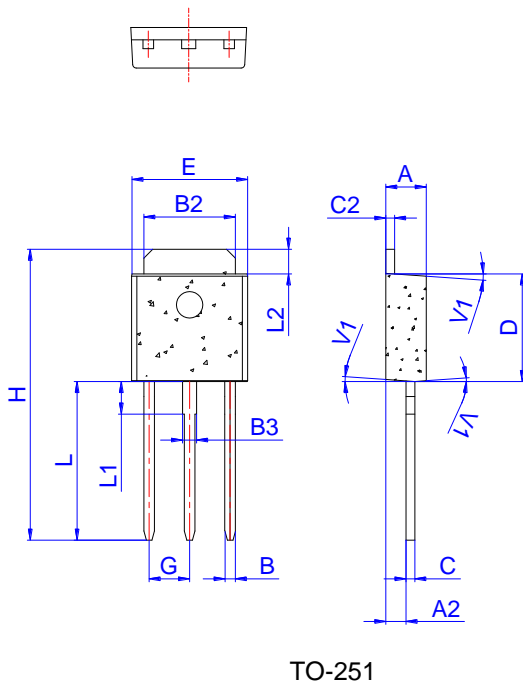
PACKAGE MECHANICAL DATA



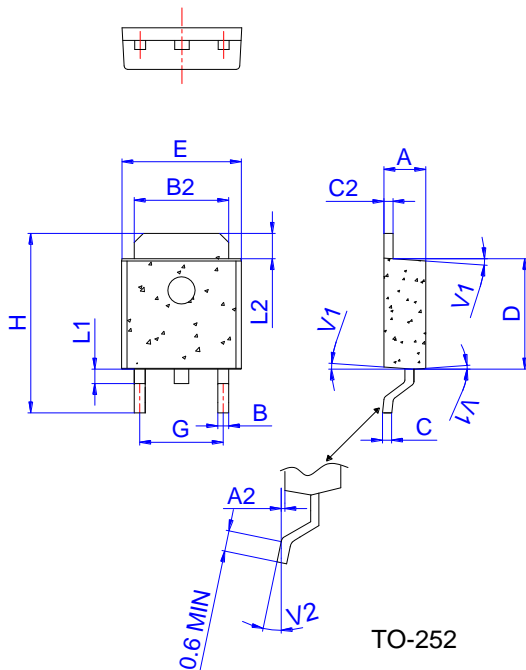
TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA

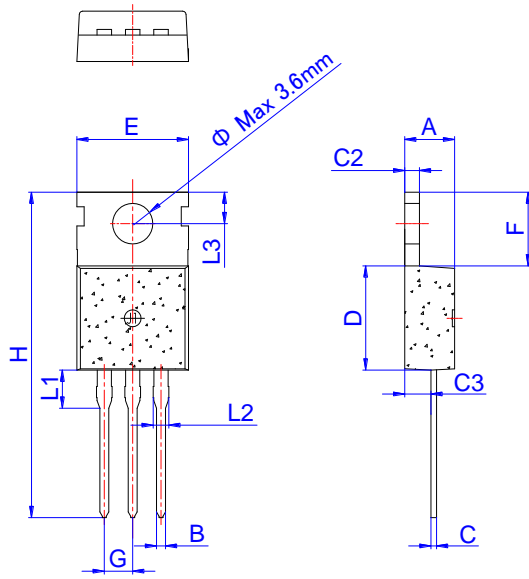


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	

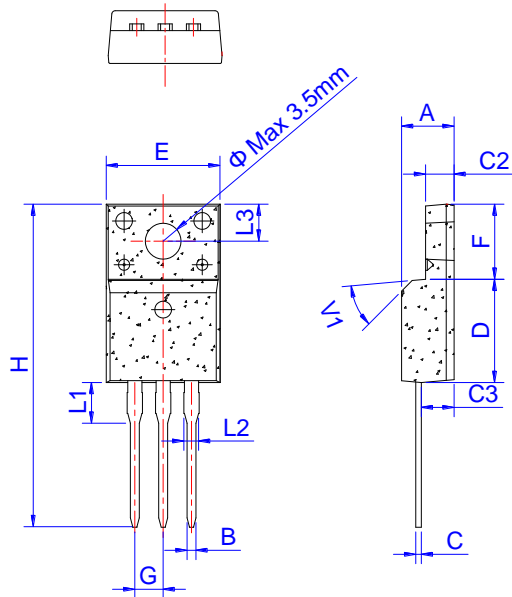


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2		0°	8°		0°	8°

PACKAGE MECHANICAL DATA

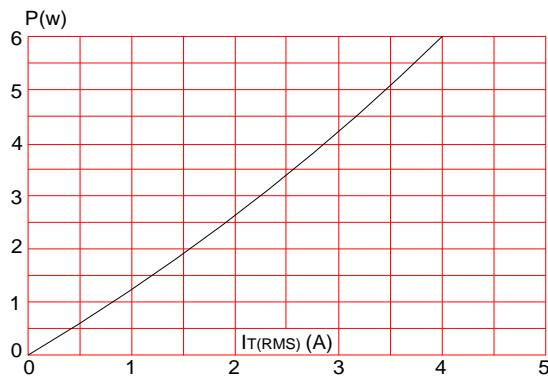


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

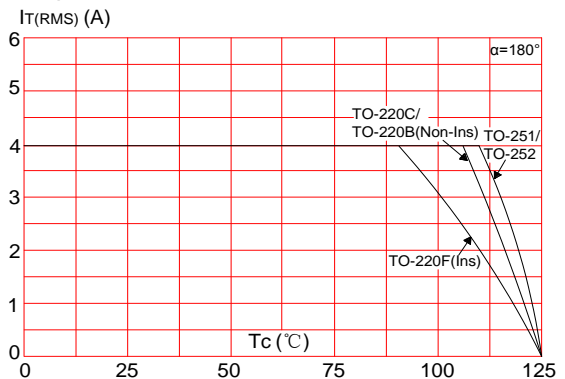


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.48		0.75	0.019		0.030
C2	2.40		2.70	0.094		0.106
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.70		10.3	0.382		0.406
F	6.40		7.00	0.252		0.276
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

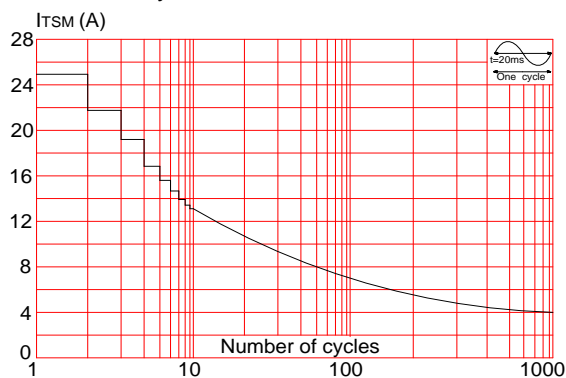
**FIG.1** Maximum power dissipation versus RMS on-state current



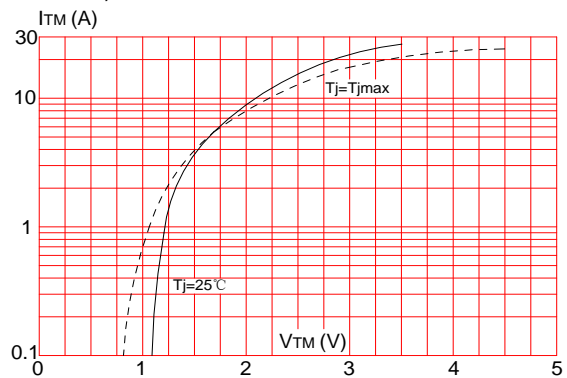
**FIG.2** RMS on-state current versus case temperature



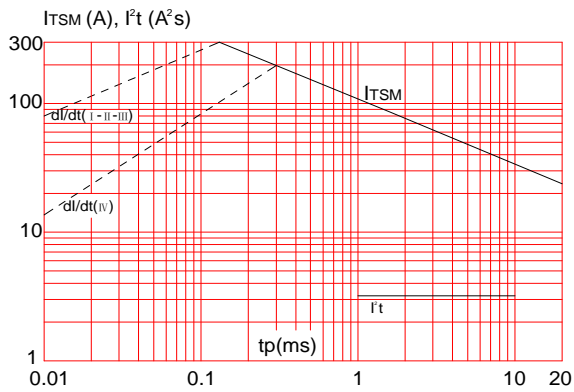
**FIG.3:** Surge peak on-state current versus number of cycles



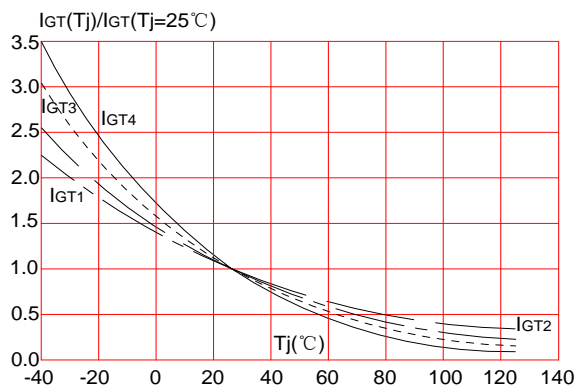
**FIG.4:** On-state characteristics (maximum values)



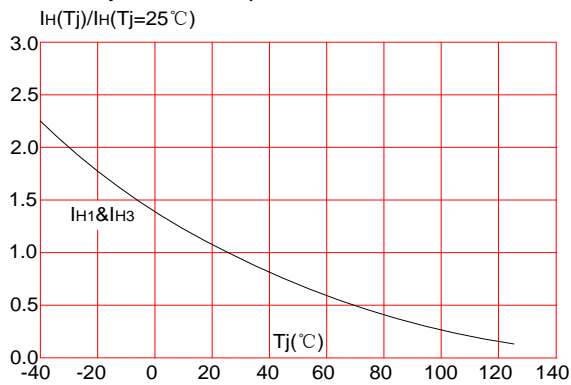
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20ms$  and corresponding value of  $I^2t$  ( I - II -III:  $di/dt < 50A/\mu s$ ; IV:  $di/dt < 10A/\mu s$ )



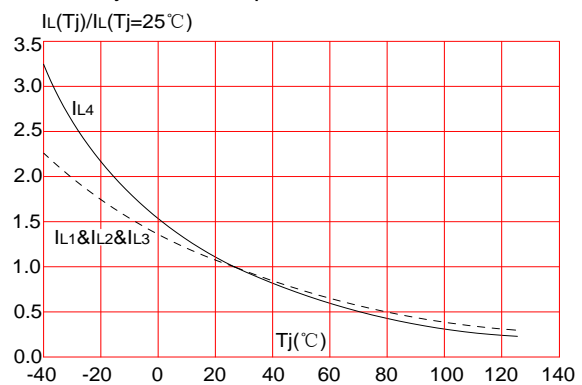
**FIG.6:** Relative variations of gate trigger current versus junction temperature




**FIG.7:** Relative variations of holding current versus junction temperature



**FIG.8:** Relative variations of latching current versus junction temperature



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